IN THE CLAIMS

Please amend claims 1 and 15-18 as follows:

1. (CURRENTLY AMENDED) A ~~Group-III nitride~~ (B, Al, Ga, In)N based light emitting diode (LED), wherein light from an emitting layer is extracted through a surface of the nitrogen face (N-face) of the ~~Group-III nitride based~~ LED and the surface of the N-face of the ~~Group-III nitride based~~ LED is structured ~~so that~~ to enhance extraction of the light ~~is extracted~~ out of the ~~Group-III nitride based LED~~ surface.

2. (PREVIOUSLY PRESENTED) The LED of claim 1, wherein the surface of the N-face is structured into one or more cones.

3. (PREVIOUSLY PRESENTED) The LED of claim 1, wherein the structured surface reduces light reflections occurring repeatedly inside the LED, and thus extracts more light out of the LED.

4. (PREVIOUSLY PRESENTED) The LED of claim 1, wherein the surface of the N-face is structured by an anisotropic etching.

5. (PREVIOUSLY PRESENTED) The LED of claim 4, wherein the anisotropic etching is a dry etching.

6. (PREVIOUSLY PRESENTED) The LED of claim 25, wherein the wet etching is a photo-enhanced chemical (PEC) etching.

7. (PREVIOUSLY PRESENTED) The LED of claim 1, wherein the N-face is an n-type layer of the LED.

8. (PREVIOUSLY PRESENTED) The LED of claim 1, wherein the N-face is prepared by a laser lift off (LLO) technique.

9. (PREVIOUSLY PRESENTED) The LED of claim 1, wherein the LED is grown on a c-plane GaN wafer and a gallium face (Ga-face) is a p-type layer.

10. (PREVIOUSLY PRESENTED) The LED of claim 1, wherein the LED is comprised of an n-type electrode, n-type layer, active region, p-type layer and p-type electrode.

11. (PREVIOUSLY PRESENTED) The LED of claim 10, wherein the n-type layer, active region and p-type layer are each comprised of a (B, Al, Ga, In)N alloy.

12. (PREVIOUSLY PRESENTED) The LED of claim 10, wherein the p-type electrode has a property of high reflection to decrease light absorption and to increase light reflection toward the surface of the n-type layer.

13. (PREVIOUSLY PRESENTED) The LED of claim 10, wherein the LED includes a current-blocking layer aligned under the n-type electrode to keep the current from concentrating below the n-type electrode, so that absorption of light emission under the n-type electrode can be avoided and extraction efficiency can be increased.

14. (PREVIOUSLY PRESENTED) The LED of claim 10, wherein the LED includes a current-confining frame made of an insulator to restrain leakage current through the sidewalls of the LED without significantly decreasing an emitting area.

15. (CURRENTLY AMENDED) The LED of claim 2, wherein the structured surface is comprised of a plurality of hexagonal shaped cones that have an angle equal to or smaller than:

$2\sin^{-1}(n_{air}/n_s)$ [[$\approx 47.2°$]]

where n_{air} is a refractive index of air and n_s is a refractive index of the ~~Group-III nitride~~ structured surface.

16. (CURRENTLY AMENDED) The LED of claim 2, wherein the structured surface is comprised of a plurality of hexagonal shaped cones that have an angle equal to or smaller than:

$$2\sin^{-1}(n_{enc}/n_s)$$

~~for epoxy~~, where n_{enc} is a refractive index of epoxy on the structured surface and n_s is a refractive index of the ~~Group-III nitride~~ structured surface.

17. (CURRENTLY AMENDED) A method of creating a ~~Group-III nitride~~ (B, Al, Ga, In)N based light emitting diode (LED), wherein light from an emitting layer is extracted through a structured surface of a nitrogen face (N-face) of the LED, comprising:

structuring the surface of the N-face after growth to extract light out of the ~~Group-III nitride based LED~~ surface.

18. (CURRENTLY AMENDED) A ~~Group-III nitride based~~ (B, Al, Ga, In)N light emitting diode (LED) comprised of an n-type electrode, n-type layer, active region, p-type layer and p-type electrode, wherein a nitrogen face (N-face) surface of the n-type layer is structured after growth, so that light from the active region is extracted through the structured N-face surface of the n-type layer.

19. (PREVIOUSLY PRESENTED) The method of claim 17, wherein the surface of the N-face is structured into one or more cones.

20. (PREVIOUSLY PRESENTED) The method of claim 17, wherein the N-face surface of the n-type layer is structured using an anisotropic etching.

21. (PREVIOUSLY PRESENTED) The method of claim 20, wherein the anisotropic etching is a dry etching.

22. (PREVIOUSLY PRESENTED) The method of claim 20, wherein the anisotropic etching is a wet etching.

23. (PREVIOUSLY PRESENTED) The method of claim 22, wherein the wet etching is a photo-enhanced chemical (PEC) etching.

24. (PREVIOUSLY PRESENTED) The method of claim 17, wherein the surface of the N-face is structured by roughening or patterning.

25. (PREVIOUSLY PRESENTED) The LED of claim 4, wherein the anisotropic etching is a wet etching.

26. (PREVIOUSLY PRESENTED) The LED of claim 1, wherein the surface of the N-face is structured by roughening or patterning.